

## The optical properties of bismuth germanium oxide single crystals

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Bi<sub>12</sub>GeO<sub>20</sub> single crystals were grown by the Czochralski technique. Suitable polishing and etching solutions were determined. Reflection spectra were recorded in the wave numbers range 20–5000 cm<sup>-1</sup>, and compared with the spectra of Bi<sub>12</sub>SiO<sub>20</sub> single crystals to study the position of the phonon modes. The optical constants of the Bi<sub>12</sub>GeO<sub>20</sub> single crystals were obtained using Kramers-Kronig analysis. The obtained results are discussed and compared with published data.

*Keywords:* Czochralski technique, bismuth germanium oxide, single crystals, optical properties, optical phonons.

### INTRODUCTION

Bismuth germanium oxide is one of perhaps ten compounds which make up the sillenite family of piezoelectric bismuth oxides which crystallise in a body centred cubic structure and possess 23 symmetry.<sup>1</sup> These oxide compounds have a congruent melting point and parameters of about 1.0 nm. They have the structure Bi<sub>12</sub>MO<sub>20</sub>, where M is Si, Ti, Ge, Mn or some other four-valence ion, or a combination of two-ions.<sup>2</sup> All members of the sillenite family, commonly called the Bi<sub>12</sub>MO<sub>20</sub> group, have space group I23.<sup>3</sup>

Bismuth germanium oxide (BGO) finds application for long delay lines because it possesses a very slow surface wave velocity. Due to its cubic structure, it is nearly isotropic to surface wave propagation, making it feasible to propagate the surface at an angle to the crystal axis as well as around curved surfaces of a plate. This enables the construction of a delay line where the surface wave follows a spiral path around the plate, making the effective length of the delay line many times longer than the physical length of the plate. Using this technique, it is possible to store a complete video frame of information from a TV broadcast. Coupling this long delay line with the appropriate circuitry to form a shift register, the information could then

be circulated and stored indefinitely. Only the information, which has changed in the television picture, need be transmitted in order to update the information stored in the BGO shift register.<sup>4</sup> Besides its memory effect, bismuth germanium oxide finds many applications in the field of optics, such as holographic storage<sup>4</sup> and two-dimensional commutation.<sup>5</sup> These applications place the most stringent requirements on the optical quality of material. The aim of this study was the study of optical properties of the obtained  $\text{Bi}_{12}\text{GeO}_{20}$  single crystals.

#### EXPERIMENTAL

$\text{Bi}_{12}\text{GeO}_{20}$  single crystals were grown by the Czochralski technique using a MSR 2 crystal puller controlled by an Eurotherm. This system keeps the crucible temperature constant to within 0.2 °C. The crystal diameter was predetermined and automatically kept constant by an additional weighing assembly continuously monitoring the crucible weight. The absolute value of the deviation from the given diameter was below 0.1 mm. The atmosphere used was air. An iridium wire was used as the crystal seed.

All crystals were grown from synthesised  $\text{Bi}_2\text{O}_3$  and  $\text{GeO}_2$ . The starting materials were mixed together in the stoichiometric ratio (6:1). The melt was contained in a platinum crucible ( $\varnothing$  4 cm, 4 cm depth), which was placed in an alumina vessel on the zircon-oxide wool. The whole system represents a kind of protection against excessive radiate heat loss. To reduce thermal gradients in the crystal and the melt, a cylindrical silica glass afterheater was installed around the system with the crucible.<sup>6</sup> The crucible was not rotated during the growth. The conditions for the growth of  $\text{Bi}_{12}\text{GeO}_{20}$  single crystals by the Czochralski technique were optimised as these depend mainly on the hydrodynamics in the melt. The pull rates were experimentally determined. After the growth run, the crystal boule was cooled at a rate about 50 °C/h down to room temperature.

The obtained crystals were cut, polished and etched. For chemical polishing a solution of  $\text{HCl} + \text{HNO}_3 + \text{H}_2\text{O}$  in the ratio 1:1:5 was found to be suitable for polishing the crystals of bismuth germanium oxide. The etching solution was  $\text{HCl} + \text{H}_2\text{O}$  in the ratio 1:5.

All the obtained crystal plates were observed in polarised light to reveal strains.

Infrared spectra were recorded using a Fourier-transform spectrometer Bomem DA8. For the far infrared region, a beamsplitter was used (the hypersplitter for the spectral range 20–700  $\text{cm}^{-1}$ ) and for the infrared standard KBr (400–5000  $\text{cm}^{-1}$ ). All spectra were obtained using a near normal incidence configuration at room temperature. For both spectral regions, Globar (SiC) was used as the source and in addition, for the far infrared region, a Hg lamp. The spectra of  $\text{Bi}_{12}\text{GeO}_{20}$  were recorded with a resolution of 1  $\text{cm}^{-1}$  while the resolution of the  $\text{Bi}_{12}\text{SiO}_{20}$  spectra was 2  $\text{cm}^{-1}$ . This influenced the signal-to-noise ratio of the obtained spectra.

#### RESULTS AND DISCUSSION

$\text{Bi}_{12}\text{GeO}_{20}$  single crystals are obtained using the Czochralski technique. The growth conditions were calculated using the hydrodynamics of the melt. It was found<sup>7</sup> experimentally that the flatter the interface is, the better the quality of the grown crystal. This is a theoretical and practical target for every grown crystal. Inappropriate growth conditions could be responsible for different defects, such as stresses in the crystal, cracks, non-homogenous impurity concentrations, core phenomena, gas-bubble entrapment, *etc.*<sup>8–11</sup> These crystals have anisotropy in the optical density and they are practically unacceptable for most optical devices. There are many theories about dark core formation, but all authors agree that the dark core is absent when the interface is flat.

The conditions for growing single crystals of  $\text{Bi}_{12}\text{GeO}_{20}$  were calculated by using the hydrodynamics of the melt.<sup>12</sup> The values of the critical diameter of the crystal and critical rotation rate were theoretically obtained using a combination of Reynolds and Grashof numbers, and found to be 1.2 cm and 20 rpm, respectively. The crystal pulling rate was determined experimentally to be 5 mm/h. In our experiments, pale yellow crystals about 12 mm in diameter were produced with a length of about 40 mm. The colour of the crystals was in accordance with published data.<sup>13</sup> The absence of a core was confirmed by observing the polished crystal plates under polarised light.

A solution of  $\text{HCl} + \text{HNO}_3 + \text{H}_2\text{O}$  in the ratio 1:1:5 was found to be suitable for the chemical polishing of the bismuth germanium oxide crystals. Many experiments were performed to find a suitable etching solution. Etching solutions of  $\text{HF} + \text{HNO}_3$  in the ratio of 2:1 and  $\text{HCl} + \text{H}_2\text{O}$  in the ratio of 1:2 were found to be unsuitable, but  $\text{HCl} + \text{H}_2\text{O}$  in the ratio 1:5 was satisfactory. Observations of the etched pits revealed that the crystals were grown in the [111] direction. Many dislocations could be seen and their investigation, together with the other crystal defects, will be published in the next article about  $\text{Bi}_{12}\text{GeO}_{20}$  single crystals.

The structure properties were obtained using X-ray analysis of powdered samples.<sup>12</sup> The unit cell of  $\text{Bi}_{12}\text{GeO}_{20}$  was calculated by the least square method using 37 reflections. Many of the reflections correspond to  $\text{Bi}_{12}\text{GeO}_{20}$  crystal with the unit cell parameter  $a = 1.014558$  nm.<sup>14</sup> Some divergence from the compared results can be explained by the fact that X-ray powder diffraction analysis gives statistical result. Our calculated results for the lattice parameter is  $a = 1.014$  nm, which is in good agreement with published data.<sup>2,14</sup> It has been reported<sup>15</sup> that only almost perfect single crystals can split X-ray reflections into  $K_{\alpha 1}$  and  $K_{\alpha 2}$  and the presence of doublets is one more confirmation of the excellent quality of the produced crystals.

The  $\text{Bi}_{12}\text{GeO}_{20}$  single crystal reflectance spectrum was recorded at room temperature (298 K) and is shown in Fig. 1.

In order to see any differences between the spectra of bismuth silicon oxide and bismuth germanium oxide, both spectra are presented one over another in Fig. 1. The spectra are almost identical except for the strong  $679\text{ cm}^{-1}$  mode in the spectrum of  $\text{Bi}_{12}\text{GeO}_{20}$ , which is missing in that of  $\text{Bi}_{12}\text{SiO}_{20}$ , and the mode at  $169\text{ cm}^{-1}$  in the  $\text{Bi}_{12}\text{SiO}_{20}$  spectrum that is absent in the  $\text{Bi}_{12}\text{GeO}_{20}$  spectrum. Also, the mode at  $820\text{ cm}^{-1}$  in the  $\text{Bi}_{12}\text{SiO}_{20}$  spectrum is nearly absent in the  $\text{Bi}_{12}\text{GeO}_{20}$  spectrum. Both modes (at  $679\text{ cm}^{-1}$  and  $820\text{ cm}^{-1}$ ) certainly represent pure oxygen vibrations.

Regarding the other infrared-active modes, the main difference concerns just three modes at about  $170$ ,  $200$  and  $280\text{ cm}^{-1}$ . The mode at  $173\text{ cm}^{-1}$  in bismuth silicon oxide almost disappears in bismuth germanium oxide. Also a mode at  $203\text{ cm}^{-1}$  is very sharp in bismuth germanium oxide, but at the same position. The mode that certainly comprises the germanium (silicon) atom vibration appears just as a knee at  $283\text{ cm}^{-1}$  in bismuth silicon oxide, whereas it is shifted to lower frequencies ( $271\text{ cm}^{-1}$ ) in bismuth germanium oxide. To a first approximation, assuming that this mode consists of pure Ge–O or Si–O vibrations and taking into account the mass differences between Ge and Si atoms,<sup>16</sup> a frequency shift of about  $25\text{ cm}^{-1}$  can

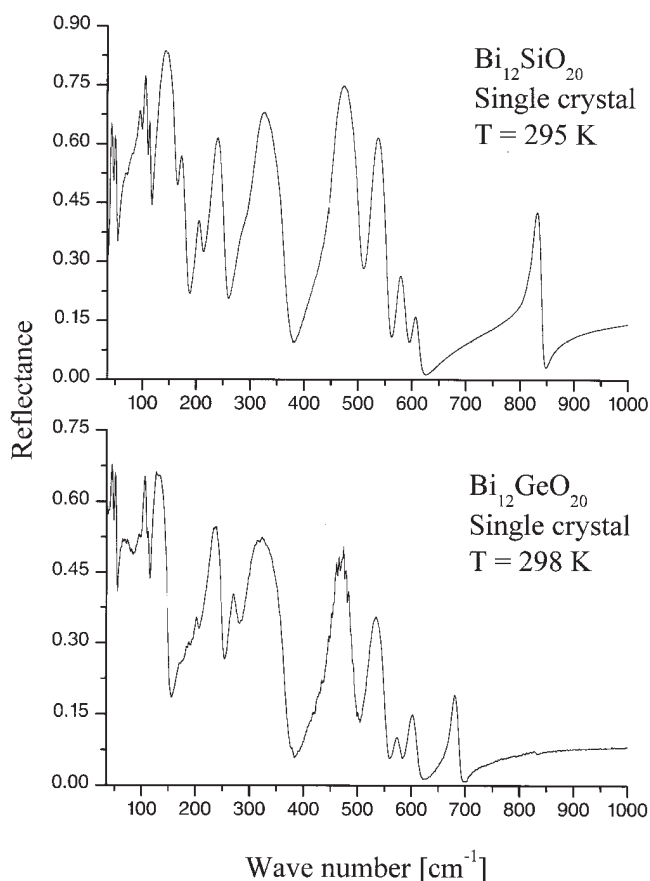


Fig. 1. The infrared reflectance spectra of  $\text{Bi}_{12}\text{GeO}_{20}$  and  $\text{Bi}_{12}\text{SiO}_{20}$  in the range 35–1000  $\text{cm}^{-1}$  at 298 K and 295 K, respectively.

be estimated. The simple calculation below, based on a crystal with two different atoms is in fairly good agreement with our experimental finding for the normal mode at 283  $\text{cm}^{-1}$  (Si). Namely, in this case one should take a phonon frequency as:

$$\omega^2 = \frac{\text{const.}}{\bar{m}} \quad (1)$$

$$\text{where } \bar{m} = \frac{m_{\text{Ge(Si)}} \cdot m_{\text{O}}}{m_{\text{Ge(Si)}} + m_{\text{O}}}$$

$$\text{Hence, one obtains } \frac{\omega_{\text{Ge-O}}}{\omega_{\text{Si-O}}} = \sqrt{\frac{\bar{m}_{\text{Si-O}}}{\bar{m}_{\text{Ge-O}}}} = 0.9 \quad (2)$$

To the best of our knowledge, the parameters of the TO and LO modes of a  $\text{Bi}_{12}\text{GeO}_{20}$  single crystal have not been published in the literature. Using Kramers-Kronig analysis, the TO and LO functions presented in Figs. 2 and 3 were obtained. The positions of the TO and LO modes are presented in Tables I and II.

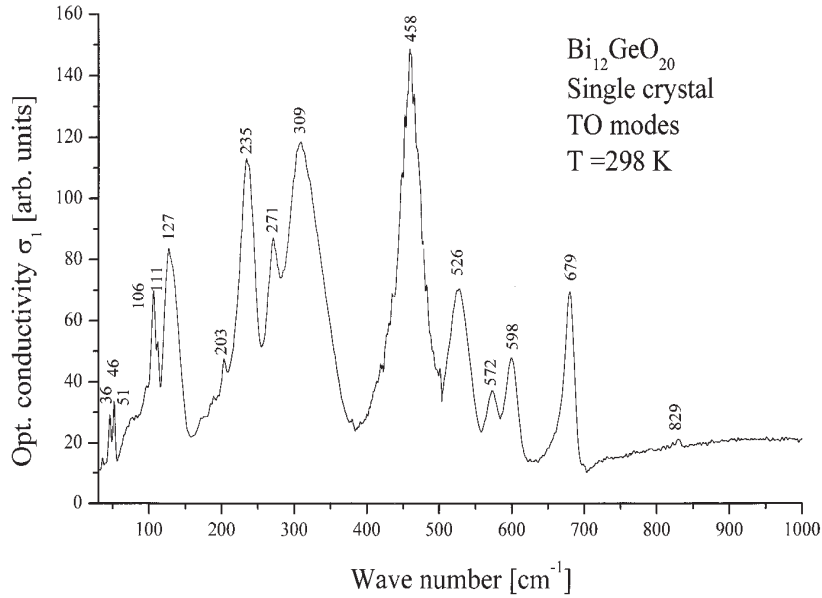


Fig. 2. TO modes ( $\omega_{\text{TO}}$ ) of a  $\text{Bi}_{12}\text{GeO}_{20}$  single crystal at 298 K.

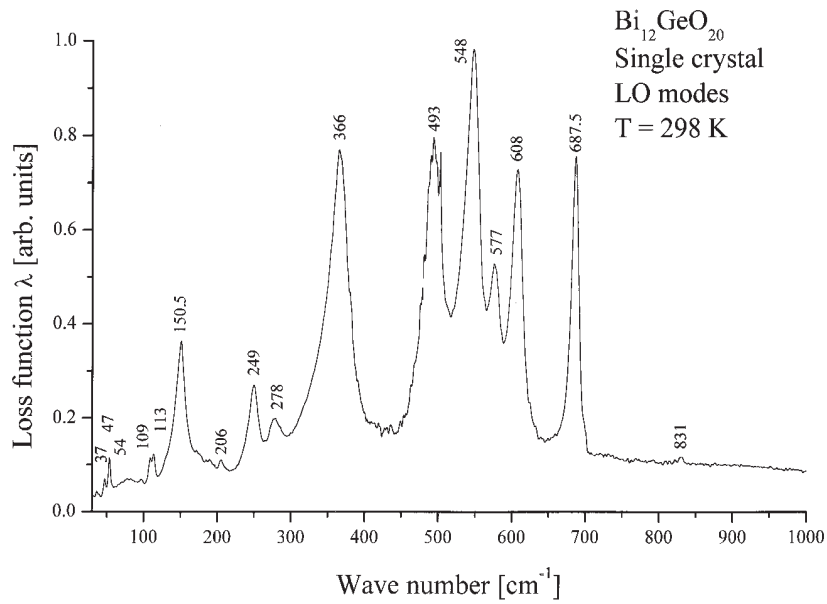


Fig. 3. LO modes ( $\omega_{\text{LO}}$ ) of a  $\text{Bi}_{12}\text{GeO}_{20}$  single crystal at 298 K.

From Figs. 2 and 3, and Tables I and II can be seen that there are 16 active infrared modes of  $\text{Bi}_{12}\text{GeO}_{20}$  single crystal at room temperature (298 K). This is in accordance with our results for the  $\text{Bi}_{12}\text{SiO}_{20}$  single crystal<sup>17</sup> where 16 active infrared modes were also found. In the literature<sup>18</sup> 10 active modes for the  $\text{Bi}_{12}\text{SiO}_{20}$

TABLE I. The transverse (TO) frequencies of the optical phonons for  $\text{Bi}_{12}\text{GeO}_{20}$  in the range 30–1000  $\text{cm}^{-1}$  at 298 K.

Number of phonon mode	Position of phonon mode/ $\text{cm}^{-1}$
1	36
2	46
3	51
4	106
5	111
6	127
7	203
8	235
9	271
10	309
11	458
12	526
13	572
14	598
15	679
16	829

TABLE II. The longitudinal (LO) frequencies of the optical phonons for  $\text{Bi}_{12}\text{GeO}_{20}$  in the range 30–1000  $\text{cm}^{-1}$  at 298 K.

Number of phonon mode	Position of phonon mode/ $\text{cm}^{-1}$
1	37
2	47
3	54
4	109
5	113
6	150.5
7	206
8	249
9	278
10	366
11	493
12	548
13	577
14	608
15	687.5
16	831

single crystal were reported and our results for both  $\text{Bi}_{12}\text{GeO}_{20}$  and  $\text{Bi}_{12}\text{SiO}_{20}$  single crystals could be very useful for understanding an assignment of the normal modes and overall characterization of these crystals.

The quality of the results obtained by Kramers-Kronig analysis were tested using the Lyddane-Sachs-Teller relation:

$$\frac{\varepsilon_0}{\varepsilon_\infty} = \prod_{j=1}^n \frac{\omega_{\text{LO},j}^2}{\omega_{\text{TO},j}^2} \quad (3)$$

The obtained values of the ratio  $\varepsilon_0/\varepsilon_\infty$  are about 9.2 and 4.4 for  $\text{Bi}_{12}\text{SiO}_{20}$  and  $\text{Bi}_{12}\text{GeO}_{20}$ , respectively. The static relative permittivities  $\varepsilon_0$ ,  $\varepsilon_\infty$  were determined from the measured reflectance at low ( $R_0$ ) and high wave numbers ( $R_\infty$ ) according to the following relation:

$$\varepsilon = \left( \frac{1 + \sqrt{R}}{1 - \sqrt{R}} \right)^2 \quad (4)$$

The obtained values for  $\text{Bi}_{12}\text{GeO}_{20}$  were  $\varepsilon_0$  about 20, and  $\varepsilon_\infty = 4.5$ , which are in a good agreement with the ratio  $\varepsilon_0/\varepsilon_\infty$  οβταινεδ υσινγ ρελατιον (3).

#### CONCLUSION

A solution  $\text{HCl} + \text{HNO}_3 + \text{H}_2\text{O}$  in the ratio 1:1:5 was found to be suitable for chemical polishing of bismuth germanium oxide crystals. The etching solution was  $\text{HCl} + \text{H}_2\text{O}$  in the ratio 1:5.

The positions of the TO and LO modes of a  $\text{Bi}_{12}\text{GeO}_{20}$  single crystal were determined. A comparison between the  $\text{Bi}_{12}\text{GeO}_{20}$  and  $\text{Bi}_{12}\text{SiO}_{20}$  reflectance spectra showed that new modes appeared in  $\text{Bi}_{12}\text{GeO}_{20}$  around  $679 \text{ cm}^{-1}$  and the mode at  $169 \text{ cm}^{-1}$  in  $\text{Bi}_{12}\text{SiO}_{20}$ . Also, a significant softening ( $12 \text{ cm}^{-1}$ ) of the  $283 \text{ cm}^{-1}$  mode on substitution of Ge for Si. The magnitude of this shift undoubtedly indicates that this band results from germanium-oxygen (silicon-oxygen) vibrations.

#### ИЗВОД

##### ОПТИЧКЕ ОСОБИНЕ МОНОКРИСТАЛА БИЗМУТ ГЕРМАНАТА

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Монокристали бизмут германата су расли техником раста кристала по Чохралском. Одређена су погодна средства за хемијско полирање и нагризање. Рефлексионни спектри су снимани у опсегу таласних бројева од  $20\text{-}5000 \text{ cm}^{-1}$  и поређени су са рефлексионим спектрима монокристала бизмут силиката да би се проучавао положај фононских модова. Оптичке константе монокристала бизмут германата су добијене

коришћењем Kramers-Kronig анализе. Добијени резултати су дискутовани и поређени са литературним подацима.

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